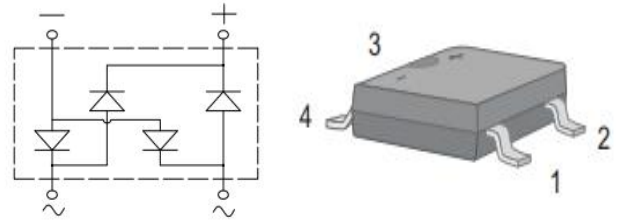




Bridge Rectifier Diode 整流桥

■ Features 特点

Glass passivated chip junction 玻璃钝化结
 High surge current capability 高浪涌电流能力
 Reflow Solder Temperature 220°C 回流焊温度 220 度
 Package 封装: MBF



■ Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	MB1F	MB2F	MB4F	MB6F	MB8F	MB10F	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	$V_{R(DC)}$	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I_F	0.8						A
Peak Surge Current 峰值浪涌电流	I_{FSM}	30						A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	90						$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	150 $^{\circ}\text{C}$, -55to+150 $^{\circ}\text{C}$						

■ Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压降	V_F		1.1		V	$I_F=0.8\text{A}$
Reverse Current ($T_A=25^{\circ}\text{C}$) 反向漏电流($T_A=125^{\circ}\text{C}$)	I_R			5 40	μA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D		13		pF	$V_R=4\text{V}, f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

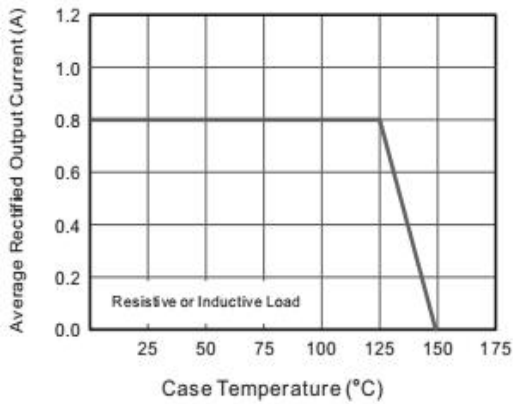


Figure 1: Forward Current Derating Curve

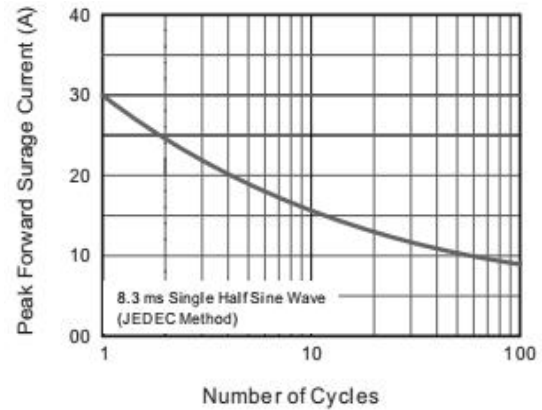


Figure 2: Peak Forward Surge Current

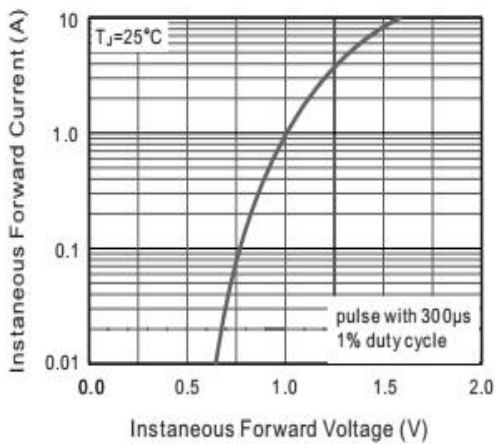


Figure 3: Instantaneous Forward Characteristics

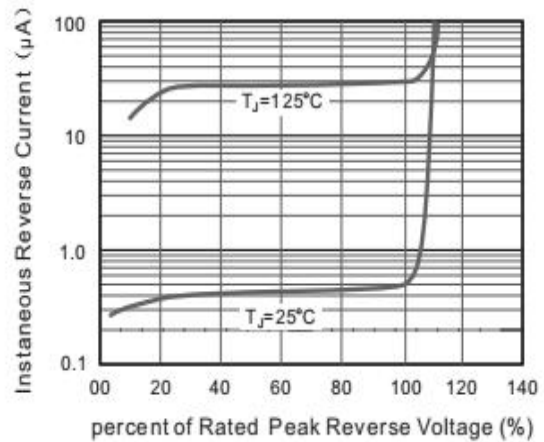


Figure 4: Reverse Leakage Characteristics

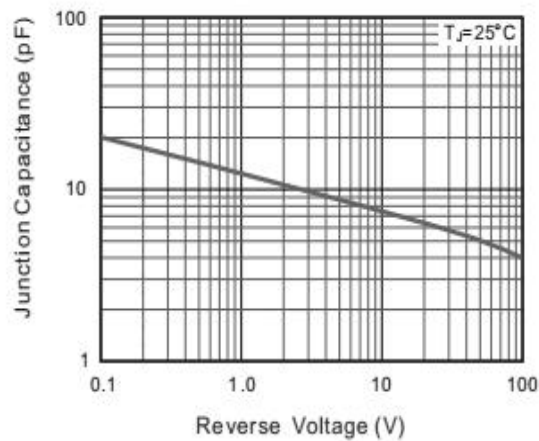
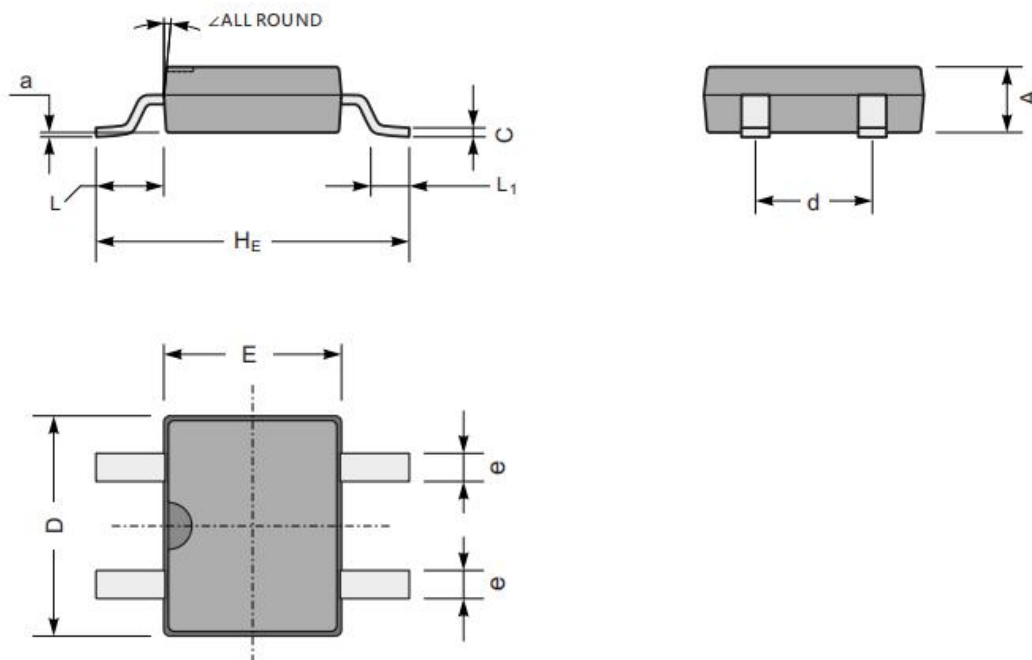


Figure 5: Junction Capacitance Characteristics

■Dimension 外形封装尺寸



MBF mechanical data

UNIT		A	C	D	E	H_E	d	e	L	L_1	a	\angle
mm	max	1.6	0.22	5.0	4.1	7.0	2.7	0.8	1.7	1.1	0.2	7°
	min	1.2	0.15	4.5	3.6	6.4	2.3	0.5	1.3	0.5	—	
mil	max	63	8.7	197	161	276	106	31	67	43	8	
	min	47	5.9	177	142	252	91	20	51	20	—	